

TSMC 98-262
Serial Number 09/325,951



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AMENDMENT AND RESPONSE TO OFFICE ACTION

TO: COMMISSIONER OF PATENTS AND TRADEMARKS
Washington, D. C. 20231

FROM: George O. Saile (Reg. No. 19,572)
20 McIntosh Drive
Poughkeepsie, NY 12603

DATE: 27 February 2001

REF: APPLICANT : Chiang et al.
SERIAL NO. : 09/325,951
ART UNIT : 2812
FILING DATE : 04/06/99
ATTY NO. : TSMC 98-262
EXAMINER : R. Pompey
TITLE : Method for Forming High Purity Silicon Oxide Field
Oxide Isolation Region

Sir:

In response to an office action mailed on 21 September 2000, please consider the following amendments and remarks pertaining to the above referenced application.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service as First Class mail in an envelope addressed to the Commissioner of Patents and Trademarks, Washington, D. C. 20231 on 28 February 2001

Stephen B. Ackerman *[Signature]*
Name Signature

Feb. 28, 2001
Date